

High Voltage IGBT with Diode

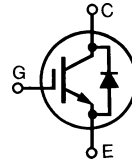
Combi Pack
Short Circuit SOA Capability

IXSK35N120AU1

$$V_{CES} = 1200 \text{ V}$$

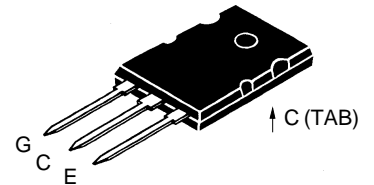
$$I_{C25} = 70 \text{ A}$$

$$V_{CE(sat)} = 4 \text{ V}$$



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1200	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1 \text{ M}\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	70	A
I_{C90}	$T_C = 90^\circ\text{C}$	35	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	140	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}$, $T_J = 125^\circ\text{C}$, $R_G = 22 \Omega$ Clamped inductive load, $L = 30 \mu\text{H}$	$I_{CM} = 70$ @ $0.8 V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = 15 \text{ V}$, $V_{CE} = 720 \text{ V}$, $T_J = 125^\circ\text{C}$ $R_G = 22 \Omega$, non repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	IGBT	300 W
		Diode	190 W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 s	300	$^\circ\text{C}$
M_d	Mounting torque	1.15/13	Nm/lb.in.
Weight		10	g

TO-264 AA



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- International standard package JEDEC TO-264 AA
- High frequency IGBT and anti-parallel FRED in one package
- 2nd generation HDMOS™ process
- Low $V_{CE(sat)}$
 - for minimum on-state conduction losses
- MOS Gate turn-on
 - drive simplicity
- Fast Recovery Epitaxial Diode (FRED)
 - soft recovery with low I_{RM}

Applications

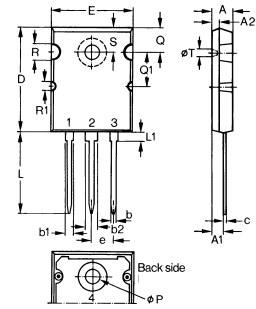
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Advantages

- Space savings (two devices in one package)
- Easy to mount with one screw (isolated mounting screw hole)
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 5 \text{ mA}$, $V_{GE} = 0 \text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 4 \text{ mA}$, $V_{CE} = V_{GE}$	4		V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$		750 μA
		$T_J = 125^\circ\text{C}$		15 mA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$, $V_{GE} = 15 \text{ V}$			4 V

Symbol	Test Conditions	Characteristic Values			
		(T _J = 25°C, unless otherwise specified)			
		min.	typ.	max.	
g_{fs}	I _C = I _{C90} ; V _{CE} = 10 V, Pulse test, t ≤ 300 μs, duty cycle ≤ 2 %	20	26	S	
I_{C(on)}	V _{GE} = 15 V, V _{CE} = 10 V		170	A	
C_{ies} C_{oes} C_{res}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		3900	pF	
			295	pF	
			60	pF	
Q_g Q_{ge} Q_{gc}	I _C = I _{C90} , V _{GE} = 15 V, V _{CE} = 0.5 V _{CES}		150	nC	
			40	60	nC
			70	100	nC
t_{d(on)} t_{ri} t_{d(off)} t_{fi} E_{off}	Inductive load, T_J = 25°C I _C = I _{C90} , V _{GE} = 15 V, L = 100 μH, V _{CE} = 0.8 V _{CES} , R _G = 2.7 Ω Note 1		80	ns	
			150	ns	
			400	900	ns
			500	700	ns
			10		mJ
t_{d(on)} t_{ri} E_{on} t_{d(off)} t_{fi} E_{off}	Inductive load, T_J = 125°C I _C = I _{C90} , V _{GE} = 15 V, L = 100 μH V _{CE} = 0.8 V _{CES} , R _G = 2.7 Ω Note 1		80	ns	
			150	ns	
			8		mJ
			400		ns
			700		ns
			15		mJ
R_{thJC} R_{thCK}				0.42 K/W K/W	

TO-264 AA Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46	BSC	.215	BSC
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

Reverse Diode (FRED)

Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
V_F	I _F = I _{C90} , V _{GE} = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %, T _J = 125°C			2.35 V
I_{RM} t_{rr}	I _F = I _{C90} , V _{GE} = 0 V, -di _F /dt = 480 A/μs V _R = 540 V I _F = 1 A; -di/dt = 200 A/μs; V _R = 30 V		32	36 A
			225	ns
			40	60 ns
R_{thJC}				0.65 K/W

IXSK 35N120AU1 characteristic curves are located in the IXSH 35N120A data sheet, Publication No. D96001DE, pages 66 - 67.